

Kazuya Masu

List of Publications by Year in descending order

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papers

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361413

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all docs

221
docs citations

221
times ranked

1006
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of current density on micro-mechanical property of electrodeposited gold film evaluated by micro-compression. Surface and Coatings Technology, 2022, 436, 128315.	4.8	2
2	Effective Young's Modulus of Complex Three Dimensional Multilayered Ti/Au Micro-Cantilevers Fabricated by Electrodeposition and the Temperature Dependency. Electrochem, 2021, 2, 216-223.	3.3	2
3	A MEMS ACCELEROMETER WITH A SINGLE AXIS TWO PROOF MASSES FOR A WIDE DETECTION RANGE. , 2021, , .		0
4	A Simplified Analytical Damping Constant Model for Perforated Proof Mass Structure of MEMS Capacitive Accelerometer by Multi-Layer Metal Technology. , 2021, , .		0
5	Co-Electrodeposition of Au-TiO ₂ Nanocomposite and the Micro-Mechanical Properties. Electrochem, 2020, 1, 388-393.	3.3	1
6	(Invited) CMOS-MEMS Based Microgravity Sensor and Its Application. ECS Transactions, 2020, 97, 91-108.	0.5	11
7	Sample geometry effect on mechanical property of gold micro-cantilevers by micro-bending test. MRS Communications, 2020, 10, 434-438.	1.8	5
8	Alloy Electroplating and Young's Modulus Characterization of AuCu Alloy Microcantilevers. Journal of the Electrochemical Society, 2020, 167, 082503.	2.9	2
9	Distributed Sensing Via Inductively Coupled Single-Transistor Chaotic Oscillators: A New Approach and Its Experimental Proof-of-Concept. IEEE Access, 2020, 8, 36536-36555.	4.2	9
10	(Invited) CMOS-MEMS Based Microgravity Sensor and Its Application. ECS Meeting Abstracts, 2020, MA2020-01, 1375-1375.	0.0	0
11	Effects of Sample Geometry on Micro-Mechanical Property of Single Crystal Gold for Applications in Microelectronics. ECS Meeting Abstracts, 2020, MA2020-02, 3307-3307.	0.0	0
12	High Strength Electrodeposited Au-Cu Alloys Evaluated by Bending Test toward Movable Micro-Components. ECS Journal of Solid State Science and Technology, 2019, 8, P412-P415.	1.8	2
13	Nanoscale Hierarchical Structure of Twins in Nanograins Embedded with Twins and the Strengthening Effect. Metals, 2019, 9, 987.	2.3	6
14	Long-term structure stability of Ti/Au layered micro-cantilever evaluated by vibration test. Microelectronic Engineering, 2019, 207, 33-36.	2.4	3
15	Cu-alloying effect on structure stability of electrodeposited gold-based micro-cantilever evaluated by long-term vibration test. Microelectronic Engineering, 2019, 215, 111001.	2.4	3
16	Strengthening of micro-cantilever by Au/Ti bi-layered structure evaluated by micro-bending test toward MEMS devices. Microelectronic Engineering, 2019, 213, 13-17.	2.4	3
17	Fabrication of Au-Cu Alloy/Ti Layered Micro-Cantilevers and the Long-Term Structure Stability. , 2019, , .		1
18	High-Sensitivity Inertial Sensor Module to Measure Hidden Micro Muscular Sounds. , 2019, , .		3

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19	Enhancement in structure stability of gold micro-cantilever by constrained fixed-end in MEMS devices. <i>Microelectronic Engineering</i> , 2018, 187-188, 105-109.	2.4	5
20	Au-Cu Alloys Prepared by Pulse Electrodeposition toward Applications as Movable Micro-Components in Electronic Devices. <i>Journal of the Electrochemical Society</i> , 2018, 165, D58-D63.	2.9	14
21	Sample size effect on micro-mechanical properties of gold electroplated with dense carbon dioxide. <i>Surface and Coatings Technology</i> , 2018, 350, 1065-1070.	4.8	8
22	Promoted bending strength in micro-cantilevers composed of nanograined gold toward MEMS applications. <i>Microelectronic Engineering</i> , 2018, 196, 20-24.	2.4	10
23	A 244-dB FOM High-Frequency Piezoelectric Resonator-Based Cascaded Fractional-N PLL With Sub-ppb-Order Channel-Adjusting Technique. <i>IEEE Journal of Solid-State Circuits</i> , 2017, 52, 1123-1133.	5.4	6
24	Design of high-frequency piezoelectric resonator-based cascaded fractional-N PLL with sub-ppb-order channel adjusting technique. , 2017, , .		1
25	A 0.5 V 5.96-GHz PLL With Amplitude-Regulated Current-Reuse VCO. <i>IEEE Microwave and Wireless Components Letters</i> , 2017, 27, 302-304.	3.2	21
26	High-Strength Electroplated Au-Cu Alloys as Micro-Components in MEMS Devices. <i>Journal of the Electrochemical Society</i> , 2017, 164, D244-D247.	2.9	9
27	Deformation behavior of electroplated gold composed of nano-columnar grains embedded in micro-columnar textures. <i>Materials Letters</i> , 2017, 202, 82-85.	2.6	4
28	Tensile tests of micro-specimens composed of electroplated gold. <i>Microelectronic Engineering</i> , 2017, 174, 6-10.	2.4	11
29	A design of spring constant arranged for MEMS accelerometer by multi-layer metal technology. , 2016, , .		3
30	Brittle Fracture of Electrodeposited Gold Observed by Micro-Compression. <i>Materials Transactions</i> , 2016, 57, 1257-1260.	1.2	6
31	A damping constant model for proof-mass structure design of MEMS inertial sensor by multi-layer metal technology. , 2016, , .		3
32	Pulse electroplating of ultra-fine grained Au films with high compressive strength. <i>Electrochemistry Communications</i> , 2016, 67, 51-54.	4.7	33
33	Path Clustering for Test Pattern Reduction of Variation-Aware Adaptive Path Delay Testing. <i>Journal of Electronic Testing: Theory and Applications (JETTA)</i> , 2016, 32, 601-609.	1.2	1
34	Enhancement of mechanical strength in Au films electroplated with supercritical carbon dioxide. <i>Electrochemistry Communications</i> , 2016, 72, 126-130.	4.7	11
35	Evaluation and modeling of adhesion layer in shock-protection structure for MEMS accelerometer. <i>Microelectronics Reliability</i> , 2016, 66, 78-84.	1.7	3
36	Development of high sensitivity CMOS-MEMS inertia sensor and its application to early-stage diagnosis of Parkinson's disease. , 2016, , .		0

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37	Development of high sensitivity CMOS-MEMS inertia sensor and its application to early-stage diagnosis of Parkinson's disease. , 2016, , .		1
38	Structure stability of high aspect ratio Ti/Au two-layer cantilevers for applications in MEMS accelerometers. Microelectronic Engineering, 2016, 159, 90-93.	2.4	12
39	A dual-axis MEMS capacitive inertial sensor with high-density proof mass. Microsystem Technologies, 2016, 22, 459-464.	2.0	18
40	An RF energy harvesting power management circuit for appropriate duty-cycled operation. Japanese Journal of Applied Physics, 2015, 54, 04DE11.	1.5	4
41	A 0.5-V 5.8-GHz low-power asymmetrical QPSK/OOK transceiver for wireless sensor network. , 2015, , .		0
42	A sub-1G CMOS-MEMS accelerometer. , 2015, , .		5
43	A 0.5-V 1.56-mW 5.5-GHz RF transceiver IC module with J-shaped folded monopole antenna. , 2015, , .		1
44	An ultra-low-power 32QAM RF transmitter. , 2015, , .		1
45	13.8 A 5.8GHz RF-powered transceiver with a 113μW 32-QAM transmitter employing the IF-based quadrature backscattering technique. , 2015, , .		12
46	0.5 V 5.8 GHz highly linear current-reuse voltage-controlled oscillator with back-gate tuning technique. Japanese Journal of Applied Physics, 2015, 54, 04DE06.	1.5	4
47	RF-Powered Transceiver With an Energy- and Spectral-Efficient IF-Based Quadrature Backscattering Transmitter. IEEE Journal of Solid-State Circuits, 2015, 50, 2975-2987.	5.4	29
48	A 0.1 G-to-20 G integrated MEMS inertial sensor. Japanese Journal of Applied Physics, 2015, 54, 087202.	1.5	9
49	E-band filters based on substrate integrated waveguide octagonal cavities loaded by complementary split-ring resonators. , 2015, , .		4
50	Assessment of Testicular Corticosterone Biosynthesis in Adult Male Rats. PLoS ONE, 2015, 10, e0117795.	2.5	15
51	An Evaluation Method of Brownian Noise in Highly Sensitive Capacitive Sensors. IEJ Transactions on Sensors and Micromachines, 2015, 135, 142-143.	0.1	3
52	A Sub-1mW Class-C-VCO-Based Low Voltage PLL with Ultra-Low-Power Digitally-Calibrated ILFD in 65nm CMOS. IEICE Transactions on Electronics, 2014, E97.C, 495-504.	0.6	1
53	A 1mG-to-20G integrated MEMS inertial sensor. , 2014, , .		0
54	A 0.5-V 2.5-GHz high-gain low-power regenerative amplifier based on Colpitts oscillator topology in 65-nm CMOS. , 2014, , .		4

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55	A 0.52-V 5.7-GHz low noise sub-sampling PLL with dynamic threshold MOSFET. , 2014, , .		9
56	A dual-axis MEMS inertial sensor using multi-layered high-density metal for an arrayed CMOS-MEMS accelerometer. , 2014, , .		3
57	An arrayed accelerometer device of a wide range of detection for integrated CMOSâ€MEMS technology. Japanese Journal of Applied Physics, 2014, 53, 027202.	1.5	11
58	Integrated CMOS-MEMS Technology and Its Applications. ECS Transactions, 2014, 61, 21-39.	0.5	26
59	Design of sub-1g microelectromechanical systems accelerometers. Applied Physics Letters, 2014, 104, .	3.3	64
60	A Variability-Aware Adaptive Test Flow for Test Quality Improvement. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2014, 33, 1056-1066.	2.7	16
61	An 8 channel, 20 V output CMOS switching driver with 3.3 V power supply using triple-well biasing techniques for integrated MEMS device control. Japanese Journal of Applied Physics, 2014, 53, 04EE13.	1.5	5
62	An ultra low power pH-monitoring IC with a duty-cycling wireless FM-transmitter. , 2014, , .		1
63	A 0.5-V 5.8-GHz ultra-low-power RF transceiver for wireless sensor network in 65nm CMOS. , 2014, , .		5
64	A capacitive CMOSâ€MEMS sensor designed by multi-physics simulation for integrated CMOSâ€MEMS technology. Japanese Journal of Applied Physics, 2014, 53, 04EE15.	1.5	7
65	A Novel Direct Injection-Locked QPSK Modulator Based on Ring VCO in 180 nm CMOS. IEEE Microwave and Wireless Components Letters, 2014, 24, 269-271.	3.2	8
66	Hypersphere Sampling for Accelerating High-Dimension and Low-Failure Probability Circuit-Yield Analysis. IEICE Transactions on Electronics, 2014, E97.C, 280-288.	0.6	1
67	State-Dependence of On-Chip Power Distribution Network Capacitance. IEICE Transactions on Electronics, 2014, E97.C, 77-84.	0.6	0
68	A Single-Platform Simulation and Design Technique for CMOS-MEMS Based on a Circuit Simulator With Hardware Description Language. Journal of Microelectromechanical Systems, 2013, 22, 755-767.	2.5	18
69	A sub-1mw 5.5-GHz PLL with digitally-calibrated ILFD and linearized varactor for low supply voltage operation. , 2013, , .		9
70	Challenges in integration of diverse functionalities on CMOS. , 2013, , .		1
71	Novel Sensor Structure and Its Evaluation for Integrated Complementary Metal Oxide Semiconductor Microelectromechanical Systems Accelerometer. Japanese Journal of Applied Physics, 2013, 52, 06GL04.	1.5	23
72	Planar Solenoidal Inductor in Radio Frequency Micro-Electro-Mechanical Systems Technology for Variable Inductor with Wide Tunable Range and High Quality Factor. Japanese Journal of Applied Physics, 2012, 51, 05EE02.	1.5	4

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73	Planar Solenoidal Inductor in Radio Frequency Micro-Electro-Mechanical Systems Technology for Variable Inductor with Wide Tunable Range and High Quality Factor. Japanese Journal of Applied Physics, 2012, 51, 05EE02.	1.5	6
74	A 21 V output charge pump circuit with appropriate well-bias supply technique in 0.18 μm Si CMOS. , 2011, , .		3
75	A Study of Digitally Controllable Radio Frequency Micro Electro Mechanical Systems Inductor. Japanese Journal of Applied Physics, 2011, 50, 05EE01.	1.5	4
76	A Study of Digitally Controllable Radio Frequency Micro Electro Mechanical Systems Inductor. Japanese Journal of Applied Physics, 2011, 50, 05EE01.	1.5	3
77	Linear Time Calculation of On-Chip Power Distribution Network Capacitance Considering State-Dependence. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2010, E93-A, 2409-2416.	0.3	2
78	A Universal Equivalent Circuit Model for Ceramic Capacitors. IEICE Transactions on Electronics, 2010, E93-C, 347-354.	0.6	0
79	Scan based process parameter estimation through path-delay inequalities. , 2010, , .		0
80	Decomposition of drain-current variation into gain-factor and threshold voltage variations. , 2010, , .		0
81	Radio Frequency Micro Electro Mechanical Systems Inductor Configurations for Achieving Large Inductance Variations and HighQ-factors. Japanese Journal of Applied Physics, 2010, 49, 05FG02.	1.5	5
82	Robust importance sampling for efficient SRAM yield analysis. , 2010, , .		18
83	Path clustering for adaptive test. , 2010, , .		10
84	Linear time calculation of state-dependent power distribution network capacitance. , 2010, , .		2
85	A Time-Slicing Ring Oscillator for Capturing Time-Dependent Delay Degradation and Power Supply Voltage Fluctuation. IEICE Transactions on Electronics, 2010, E93-C, 324-331.	0.6	0
86	An 8.9mW 25Gb/s inductorless 1:4 DEMUX in 90nm CMOS. , 2009, , .		5
87	Low temperature deposited Zr O_2 film applicable to extremely thin barrier for copper interconnect. Applied Surface Science, 2009, 256, 1222-1226.	6.1	19
88	S-Parameter-Based Modal Decomposition of Multiconductor Transmission Lines and Its Application to De-Embedding. , 2009, , .		7
89	Design of CMOS inverter-based output buffers adapting the cherry-hooper broadbanding technique. , 2009, , .		11
90	An Adaptive Test for Parametric Faults Based on Statistical Timing Information. , 2009, , .		12

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91	On-die parameter extraction from path-delay measurements. , 2009, , .		20
92	Characterization of On-Chip Multiport Inductors for Small-Area RF Circuits. IEEE Transactions on Circuits and Systems I: Regular Papers, 2009, 56, 1590-1597.	5.4	8
93	SMAFTI packaging technology for new interconnect hierarchy. , 2009, , .		11
94	Accurate Array-Based Measurement for Subthreshold-Current of MOS Transistors. IEEE Journal of Solid-State Circuits, 2009, 44, 2977-2986.	5.4	17
95	Inter-Chip Wiring Technology for 3-D LSI. Electrochemistry, 2009, 77, 812-817.	1.4	0
96	Physical design challenges to nano-CMOS circuits. IEICE Electronics Express, 2009, 6, 703-720.	0.8	6
97	Tunable CMOS LNA Using a Variable Inductor for a Reconfigurable RF Circuit. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 401-410.	0.3	0
98	Analytical Estimation of Path-Delay Variation for Multi-Threshold CMOS Circuits. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 1031-1038.	0.3	0
99	One-Shot Voltage-Measurement Circuit Utilizing Process Variation. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 1024-1030.	0.3	0
100	2-Port Modeling Technique for Surface-Mount Passive Components Using Partial Inductance Concept. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2009, E92-A, 976-982.	0.3	0
101	Physical Modeling of MEMS Variable Inductor. IEEE Transactions on Circuits and Systems II: Express Briefs, 2008, 55, 419-422.	3.0	8
102	An 8Gbps 2.5mW on-chip pulsed-current-mode transmission line interconnect with a stacked-switch Tx. , 2008, , .		4
103	An over-12-Gbps on-chip transmission line interconnect with a pre-emphasis technique in 90 nm CMOS. , 2008, , .		8
104	A Bidirectional- and Multi-Drop-Transmission-Line Interconnect for Multipoint-to-Multipoint On-Chip Communications. IEEE Journal of Solid-State Circuits, 2008, 43, 1020-1029.	5.4	53
105	LVDS-type on-chip transmission line interconnect with passive equalizers in 90nm CMOS process. , 2008, , .		0
106	On-chip differential and common mode voltage measurement using off-chip referenced twin probing. , 2008, , .		3
107	A Low-Power Differential Transmission Line Interconnect Using Wafer Level Package Technology. , 2008, , .		0
108	A MOS transistor array with pico-ampere order precision for accurate characterization of leakage current variation. , 2008, , .		4

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109	A 1.7-GHz 1.5-mW digitally-controlled FBAR oscillator with 0.03-ppb resolution. , 2008, , .		8
110	Accurate parasitic inductance determination of a ceramic capacitor through 2-port measurements. , 2008, , .		3
111	A low phase noise LC-VCO with a high-Q inductor fabricated by wafer level package technology. , 2008, , .		3
112	One-Chip Integration of Rapid Diagnosis Infectious-Disease Chip Based on New Phenomena of DNA Trap and Denature in Nanogaps. Japanese Journal of Applied Physics, 2008, 47, 3214-3219.	1.5	2
113	Non-invasive direct probing for on-chip voltage measurement. , 2008, , .		0
114	Determination of optimal polynomial regression function to decompose on-die systematic and random variations. , 2008, , .		1
115	Substrate-geometry aware 2-port modeling for surface-mount passive components. , 2008, , .		3
116	Layout-Aware Compact Model of MOSFET Characteristics Variations Induced by STI Stress. IEICE Transactions on Electronics, 2008, E91-C, 1142-1150.	0.6	8
117	Reconfigurable RF CMOS Circuit for Cognitive Radio. IEICE Transactions on Communications, 2008, E91-B, 10-13.	0.7	5
118	An Evaluation Method of the Number of Monte Carlo STA Trials for Statistical Path Delay Analysis. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2008, E91-A, 957-964.	0.3	2
119	Application of Correlation-Based Regression Analysis for Improvement of Power Distribution Network. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2008, E91-A, 951-956.	0.3	1
120	Adaptable wire-length distribution with tunable occupation probability. , 2007, , .		2
121	Improvement of power distribution network using correlation-based regression analysis. , 2007, , .		1
122	On-Chip Yagi-Uda Antenna for Horizontal Wireless Signal Transmission in Stacked Multi Chip Packaging. Japanese Journal of Applied Physics, 2007, 46, 2283-2286.	1.5	0
123	A 5.2 GHz CMOS Low Noise Amplifier with High-Q Inductors Embedded in Wafer-Level Chip-Scale Package. , 2007, , .		0
124	A MOS Transistor-Array for Accurate Measurement of Subthreshold Leakage Variation. , 2007, , .		5
125	A Low-Latency and High-Power-Efficient On-Chip LVDS Transmission Line Interconnect for an RC Interconnect Alternative. , 2007, , .		12
126	Design of High-Density Interconnects for High-Speed Transmission. , 2007, , .		1

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127	A 8-Gbps Low-Latency Multi-Drop On-Chip Transmission Line Interconnect with 1.2-mW Two-Way Transceivers. , 2007, , .		4
128	Reconfigurable CMOS Low Noise Amplifier Using Variable Bias Circuit for Self Compensation. , 2007, , .		0
129	A Multi-Drop Transmission-Line Interconnect in Si LSI. , 2007, , .		2
130	A Low-Power Low-Phase-Noise CMOS VCO using RF SiP Technology. , 2007, , .		3
131	A Wideband CMOS LC-VCO Using Variable Inductor. , 2007, , .		3
132	Small-Area CMOS RF Distributed Mixer Using Multi-Port Inductors. , 2007, , .		2
133	Low-Loss Distributed Constant Passive Devices Using Wafer-Level Chip Scale Package Technology. IEICE Transactions on Electronics, 2007, E90-C, 641-643.	0.6	0
134	Weakness Identification for Effective Repair of Power Distribution Network. Lecture Notes in Computer Science, 2007, , 222-231.	1.3	3
135	A batteryless wireless communication circuit for measurement of gastric acid. , 2006, , .		0
136	Estimation of Power Reduction by On-Chip Transmission Line for 45nm Technology. Lecture Notes in Computer Science, 2006, , 181-190.	1.3	0
137	A 0.98 to 6.6 Hz Tunable Wideband VCO in a 180nm CMOS Technology for Reconfigurable Radio Transceiver. , 2006, , .		16
138	A Loss Optimization Method Using WD Product for On-Chip Differential Transmission Line Design. , 2006, , .		3
139	On-Chip High-Q Variable Inductor Using Wafer-Level Chip-Scale Package Technology. IEEE Transactions on Electron Devices, 2006, 53, 2401-2406.	3.0	31
140	Optimization Methodology of Layer Numbers with Circuit/Process Co-Design. Japanese Journal of Applied Physics, 2006, 45, 2476-2480.	1.5	0
141	Improvement of Variable Ratio of On-Chip Variable Inductors Using Side Shield. Japanese Journal of Applied Physics, 2006, 45, 5720-5723.	1.5	1
142	Zero-Crosstalk Bus Line Structure for Global Interconnects in Si Ultra Large Scale Integration. Japanese Journal of Applied Physics, 2006, 45, 4977-4981.	1.5	2
143	A 6.5-mW 5-Gbps On-Chip Differential Transmission Line Interconnect with a Low-Latency Asymmetric Tx in a 180nm CMOS Technology. , 2006, , .		12
144	High-Crosstalk Robustness Transmission Line Interconnect in Si LSI using Zero-Crosstalk Structure. , 2006, , .		1

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145	RF Passive Components Using Metal Line on Si CMOS. IEICE Transactions on Electronics, 2006, E89-C, 681-691.	0.6	13
146	Statistical Modeling of a Via Distribution for Yield Estimation. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2006, E89-A, 3579-3584.	0.3	0
147	Prediction of delay time for future LSI using on-chip transmission line interconnects. , 2005, , .		2
148	A dynamic reconfigurable RF circuit architecture. , 2005, , .		13
149	Small-Area Inductor for Silicon CMOS Chips. Japanese Journal of Applied Physics, 2005, 44, 2766-2769.	1.5	3
150	RF Attenuation Characteristics for In Vivo Wireless Healthcare Chip. Japanese Journal of Applied Physics, 2005, 44, 5275-5277.	1.5	9
151	In Vivo Batteryless Wireless Communication System for Bio-MEMS Sensors. Japanese Journal of Applied Physics, 2005, 44, 2879-2882.	1.5	8
152	Evaluation of on-chip transmission line interconnect using wire length distribution. , 2005, , .		3
153	4 Gbps On-Chip Interconnection using Differential Transmission Line. , 2005, , .		15
154	A Reconfigurable RF Circuit Architecture for Dynamic Power Reduction. , 2005, , .		1
155	Twisted Differential Transmission Line Structure for Global Interconnect in Si LSI. Japanese Journal of Applied Physics, 2005, 44, 2774-2779.	1.5	3
156	A 1.3-2.8 GHz Wide Range CMOS LC-VCO Using Variable Inductor. , 2005, , .		18
157	Circuit Performance Prediction Considering Core Utilization with Interconnect Length Distribution Model. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3358-3366.	0.3	1
158	Wire Length Distribution Model for System LSI. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3445-3452.	0.3	2
159	Wide Tuning Range LC-VCO Using Variable Inductor for Reconfigurable RF Circuit. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 507-512.	0.3	21
160	Evaluation of X Architecture Using Interconnect Length Distribution. IEICE Transactions on Fundamentals of Electronics, Communications and Computer Sciences, 2005, E88-A, 3437-3444.	0.3	0
161	Variable RF Inductor on Si CMOS Chip. Japanese Journal of Applied Physics, 2004, 43, 2293-2296.	1.5	24
162	Inductance-Tuned LC-VCO for Reconfigurable RF Circuit Design. IEICE Electronics Express, 2004, 1, 156-159.	0.8	6

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163	Fabrication and evaluation of an on-chip micro-variable inductor. <i>Microelectronic Engineering</i> , 2003, 67-68, 582-587.	2.4	22
164	On-Chip Variable Inductor Using Microelectromechanical Systems Technology. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 2190-2192.	1.5	39
165	Equivalent Circuit Analysis of RF-Integrated Inductors with/without Ferromagnetic Material. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 2210-2213.	1.5	14
166	Lower Boundary of Supply Voltage in Digital ULSI Based on the Communication Theory. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L1133-L1135.	1.5	1
167	Variable RF Inductor on Si CMOS Chip. , 2003, , .		5
168	New binary sequences with zero-correlation duration for approximately synchronised CDMA. <i>Electronics Letters</i> , 2000, 36, 991.	1.0	54
169	Novel Low-Power Switched-Current Matched Filter for Direct-Sequence Code-Division-Multiple-Access Wireless Communication. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 2301-2304.	1.5	4
170	Crystallographic Structures and Parasitic Resistances of Self-Aligned Silicide TiSi ₂ /Self-Aligned Nitrided Barrier Layer/Selective Chemical Vapor Deposited Aluminum in Fully Self-Aligned Metallization Metal Oxide Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 5835-5838.	1.5	0
171	Reliability of Single Electron Transistor Circuits Based on Eb/NO-Bit Error Rate Characteristics. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 403-405.	1.5	5
172	Superiority of DMAH to DMEAA for al CVD technology. <i>Materials Science in Semiconductor Processing</i> , 1999, 2, 303-308.	4.0	10
173	Self-Aligned 10-nm Barrier Layer Formation Technology for Fully Self-Aligned Metallization Metal-Oxide-Semiconductor Field-Effect-Transistor. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 3264-3267.	1.5	1
174	AlN epitaxial growth on atomically flat initially nitrided $\hat{\pm}$ -Al ₂ O ₃ wafer. <i>Applied Surface Science</i> , 1997, 117-118, 540-545.	6.1	19
175	Precursor design and selective aluminum CVD. <i>Vacuum</i> , 1995, 46, 1249-1253.	3.5	12
176	High-Rate Deposition of High-Quality Silicon Nitride Film at Room Temperature by Quasi-Remote Plasma Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 6824-6826.	1.5	2
177	Transmission Electron Microscopic Observation of α -Al ₂ O ₃ Heteroepitaxial Interface with Initial-Nitriding AlN Layer. <i>Japanese Journal of Applied Physics</i> , 1995, 34, L760-L763.	1.5	38
178	Atomic hydrogen resist process with electron beam lithography for selective Al patterning. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994, 12, 3270.	1.6	9
179	Contribution of free electrons to Al CVD on a Si surface by photo-excitation. <i>Applied Surface Science</i> , 1994, 79-80, 237-243.	6.1	17
180	Silicon dioxide film deposited by photoassisted microwave plasma CVD using TEOS. <i>Applied Surface Science</i> , 1994, 79-80, 327-331.	6.1	6

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181	Short-channel-effect free 0.18 μm MOSFET by temperature-dimension combination scaling theory: design and experiment. IEEE Electron Device Letters, 1994, 15, 202-205.	3.9	3
182	Temperature scaling concept of MOSFET. European Physical Journal Special Topics, 1994, 04, C6-3-C6-12.	0.2	1
183	Area-selective CVD of metals. Thin Solid Films, 1993, 228, 312-318.	1.8	32
184	Area-Selective Aluminum Patterning Using Atomic Hydrogen Resist. Japanese Journal of Applied Physics, 1993, 32, 278-281.	1.5	22
185	Low-Temperature Metal-Oxide-Semiconductor Field-Effect Transistor Operation by Temperature Scaling Theory. Japanese Journal of Applied Physics, 1993, 32, 419-422.	1.5	2
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